

# 74LVC1G58

Low-power configurable multiple function gate

Rev. 8 — 22 April 2014

Product data sheet

## 1. General description

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The 74LVC1G58 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XOR, inverter and buffer. All inputs can be connected to  $V_{CC}$  or GND.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

All inputs (A, B and C) are Schmitt trigger inputs. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

## 2. Features and benefits

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- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V.
- $\pm 24$  mA output drive ( $V_{CC} = 3.0$  V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from  $-40$  °C to  $+85$  °C and  $-40$  °C to  $+125$  °C.



### 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G58GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC1G58GV	-40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74LVC1G58GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC1G58GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74LVC1G58GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74LVC1G58GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202

### 4. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74LVC1G58GW	YK
74LVC1G58GV	V58
74LVC1G58GM	YK
74LVC1G58GF	YK
74LVC1G58GN	YK
74LVC1G58GS	YK

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram

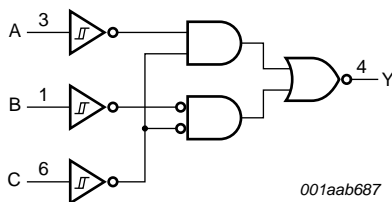
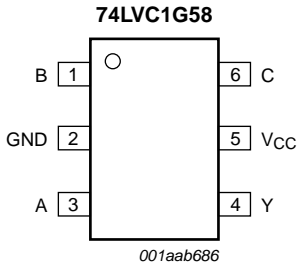
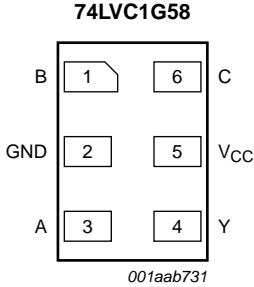
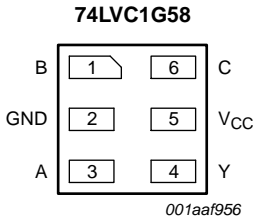


Fig 1. Logic symbol

## 6. Pinning information

### 6.1 Pinning

 <p>74LVC1G58</p> <p>001aab686</p> <p>Fig 2. Pin configuration SOT363 and SOT457</p>	 <p>74LVC1G58</p> <p>001aab731</p> <p>Transparent top view</p> <p>Fig 3. Pin configuration SOT886</p>	 <p>74LVC1G58</p> <p>001aaf956</p> <p>Transparent top view</p> <p>Fig 4. Pin configuration SOT891, SOT1115 and SOT1202</p>
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### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V <sub>CC</sub>	5	supply voltage
C	6	data input

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

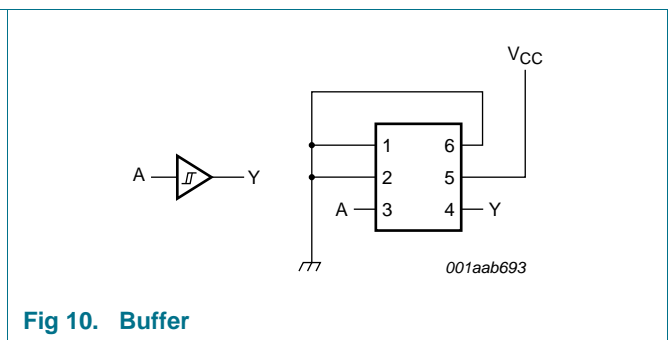
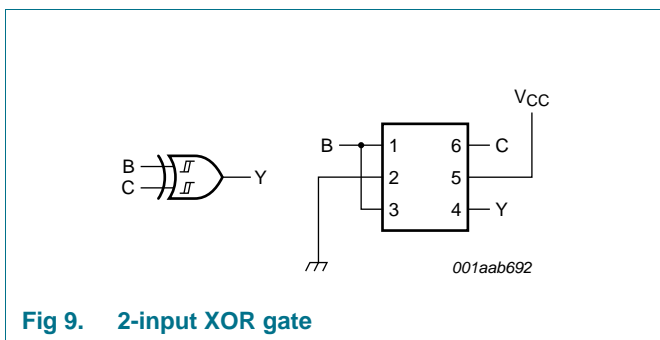
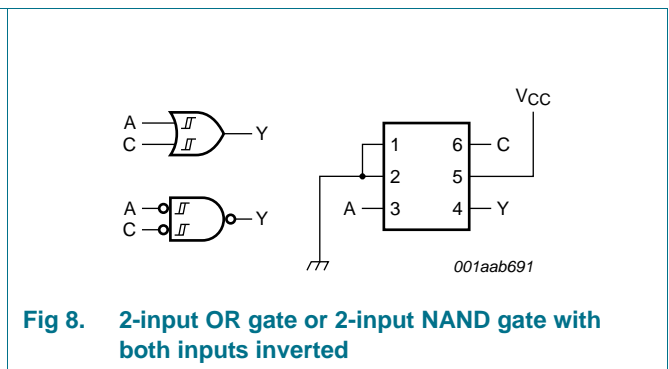
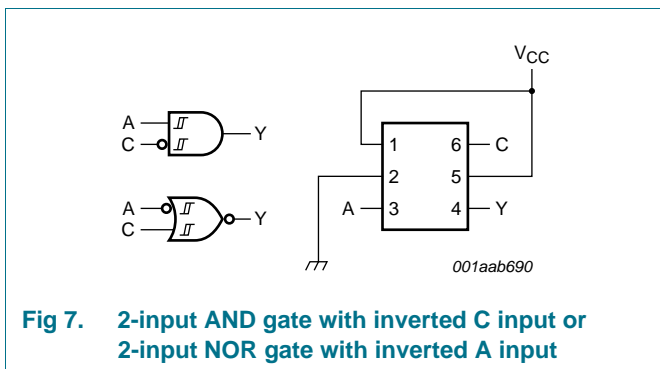
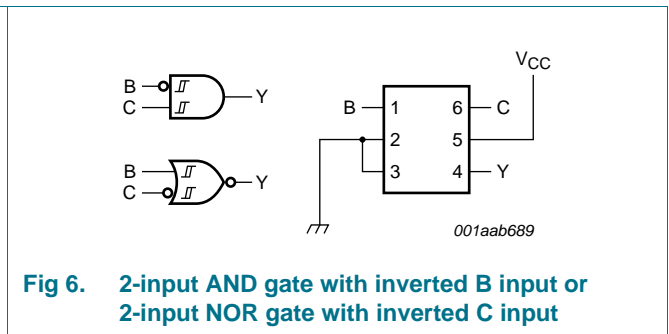
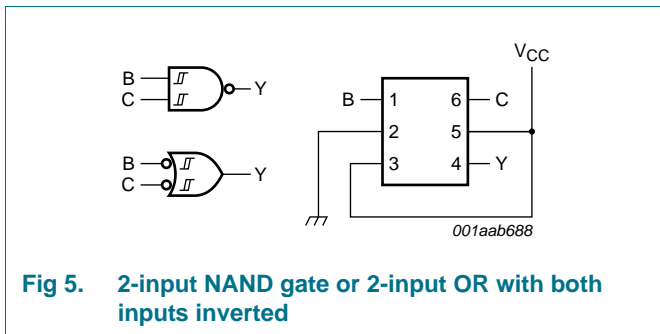
Inputs			Output
C	B	A	Y
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	L
H	H	H	L

[1] H = HIGH voltage level; L = LOW voltage level

7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input NAND	see <a href="#">Figure 5</a>
2-input NAND with both inputs inverted	see <a href="#">Figure 8</a>
2-input AND with inverted input	see <a href="#">Figure 6</a> and <a href="#">7</a>
2-input NOR with inverted input	see <a href="#">Figure 6</a> and <a href="#">7</a>
2-input OR	see <a href="#">Figure 8</a>
2-input OR with both inputs inverted	see <a href="#">Figure 5</a>
2-input XOR	see <a href="#">Figure 9</a>
Buffer	see <a href="#">Figure 10</a>
Inverter	see <a href="#">Figure 11</a>



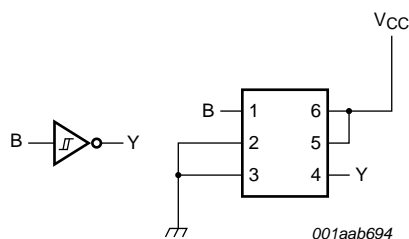


Fig 11. Inverter

## 8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		[1] -0.5	+6.5	V
$I_{OK}$	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
$V_O$	output voltage	Active mode	[1][2] -0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	±50	mA
$I_{CC}$	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When  $V_{CC} = 0$  V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For SC-88 and SC-74 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.  
For XSON6 packages: above 118 °C the value of  $P_{tot}$  derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage		1.65	-	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_O$	output voltage	Active mode	0	-	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	-	5.5	V
$T_{amb}$	ambient temperature		-40	-	+125	°C

## 10. Static characteristics

**Table 8. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.3	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.55	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	1.2	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	2.2	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.3	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.8	-	-	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	±0.1	±5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 5.5 V; V <sub>CC</sub> = 0 V	-	±0.1	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 5.5 V	-	5	500	μA
C <sub>I</sub>	input capacitance		-	2.5	-	pF
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.7	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.6	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.8	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	0.95	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.7	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	1.9	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.0	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.4	-	-	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	±100	μA

**Table 8. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 5.5 V; V <sub>CC</sub> = 0 V	-	-	±200	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	-	200	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 5.5 V	-	-	5000	μA

[1] Typical values are measured at maximum V<sub>CC</sub> and T<sub>amb</sub> = 25 °C.

## 11. Dynamic characteristics

**Table 9. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 13](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	A, B, C to Y; see <a href="#">Figure 12</a> <sup>[2]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	6.0	14.4	1.0	18.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.5	3.5	8.3	0.5	10.4	ns
		V <sub>CC</sub> = 2.7 V	0.5	4.2	8.5	0.5	10.6	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.5	3.8	6.3	0.5	7.9	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.5	3.0	5.1	0.5	6.4	ns
C <sub>PD</sub>	power dissipation capacitance	V <sub>CC</sub> = 3.3 V; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[3]</sup>	-	20	-	-	-	pF

[1] Typical values are measured at nominal V<sub>CC</sub> and at T<sub>amb</sub> = 25 °C.

[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>

[3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

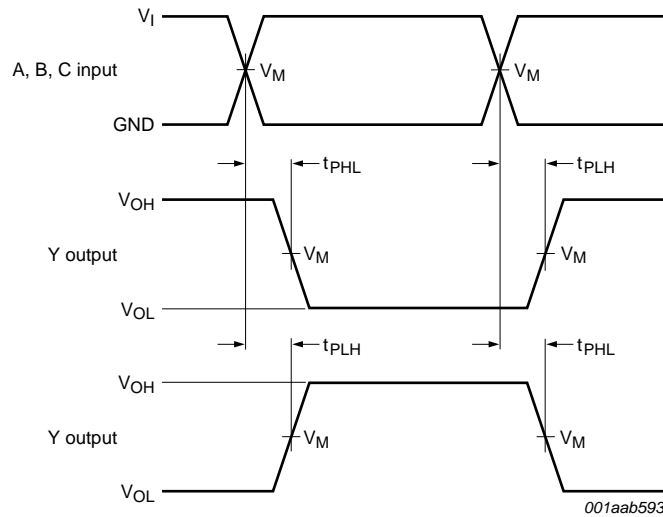
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of outputs.

12. Waveforms



Measurement points are given in [Table 10](#).

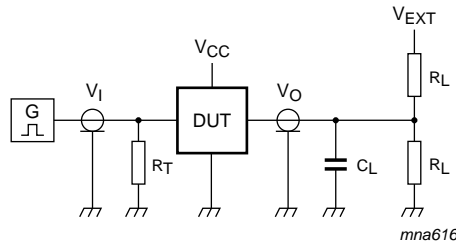
$V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

Fig 12. Input A, B, C to output Y propagation delay times

Table 10. Measurement points

Supply voltage	Input	Output
$V_{CC}$	$V_M$	$V_M$
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$





Test data is given in [Table 11](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 13. Test circuit for measuring switching times**

**Table 11. Test data**

Supply voltage	Input		Load		$V_{EXT}$
$V_{CC}$	$V_I$	$t_r = t_f$	$C_L$	$R_L$	$t_{PLH}, t_{PHL}$
1.65 V to 1.95 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	1 k $\Omega$	open
2.3 V to 2.7 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	500 $\Omega$	open
2.7 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
3.0 V to 3.6 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
4.5 V to 5.5 V	$V_{CC}$	$\leq 2.5$ ns	50 pF	500 $\Omega$	open

### 13. Transfer characteristics

**Table 12. Transfer characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
$V_{T+}$	positive-going threshold voltage	see <a href="#">Figure 14</a> , <a href="#">Figure 15</a> , <a href="#">Figure 16</a> and <a href="#">Figure 17</a>						
		$V_{CC} = 1.8$ V	0.70	1.02	1.20	0.67	1.20	V
		$V_{CC} = 2.3$ V	1.11	1.42	1.60	1.08	1.60	V
		$V_{CC} = 3.0$ V	1.50	1.79	2.00	1.47	2.00	V
		$V_{CC} = 4.5$ V	2.16	2.52	2.74	2.13	2.74	V
$V_{T-}$	negative-going threshold voltage	see <a href="#">Figure 14</a> , <a href="#">Figure 15</a> , <a href="#">Figure 16</a> and <a href="#">Figure 17</a>						
		$V_{CC} = 1.8$ V	0.30	0.53	0.72	0.30	0.75	V
		$V_{CC} = 2.3$ V	0.58	0.77	1.00	0.58	1.03	V
		$V_{CC} = 3.0$ V	0.80	1.04	1.30	0.80	1.33	V
		$V_{CC} = 4.5$ V	1.21	1.55	1.90	1.21	1.93	V
	$V_{CC} = 5.5$ V	1.45	1.86	2.29	1.45	2.32	V	

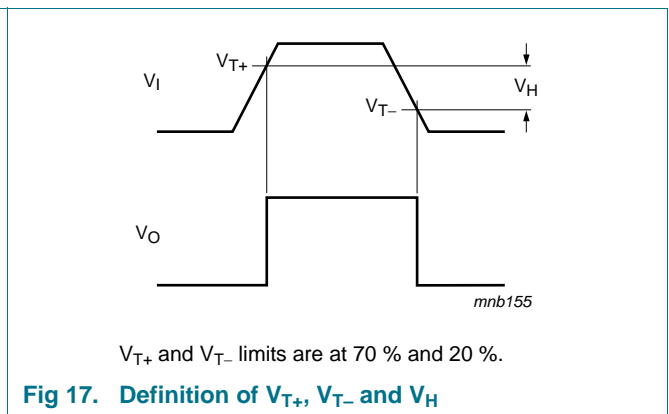
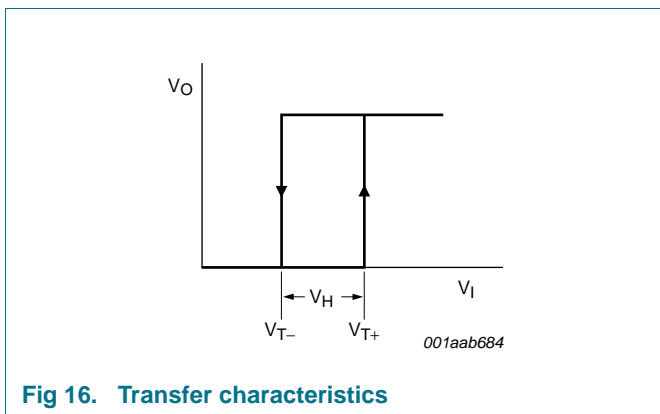
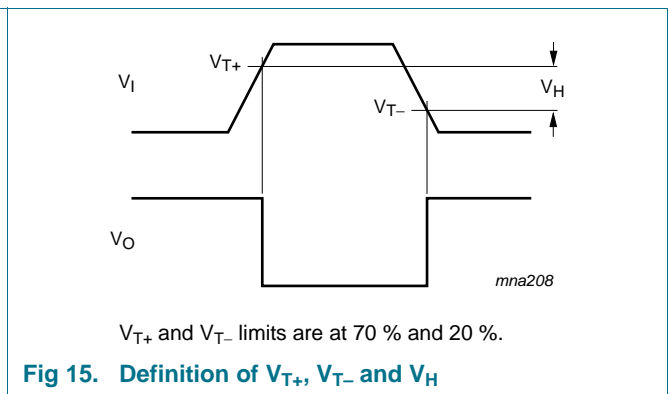
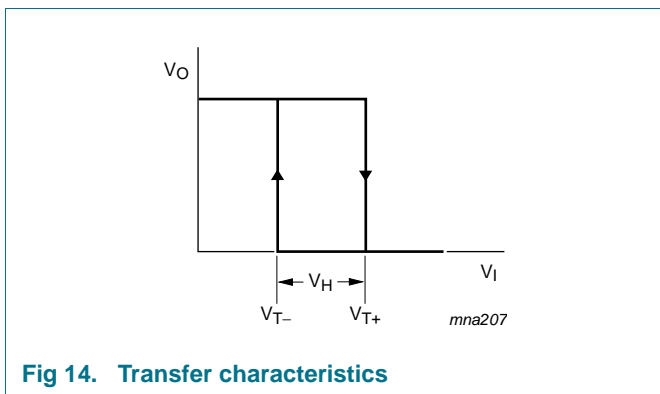
**Table 12. Transfer characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
V <sub>H</sub>	hysteresis voltage	(V <sub>T+</sub> - V <sub>T-</sub> ); see <a href="#">Figure 14</a> , <a href="#">Figure 15</a> , <a href="#">Figure 16</a> and <a href="#">Figure 17</a>						
		V <sub>CC</sub> = 1.8 V	0.30	0.48	0.62	0.23	0.62	V
		V <sub>CC</sub> = 2.3 V	0.40	0.64	0.80	0.34	0.80	V
		V <sub>CC</sub> = 3.0 V	0.50	0.75	1.00	0.44	1.00	V
		V <sub>CC</sub> = 4.5 V	0.71	0.97	1.20	0.65	1.20	V
		V <sub>CC</sub> = 5.5 V	0.71	1.13	1.40	0.65	1.40	V

[1] Typical values are measured at T<sub>amb</sub> = 25 °C.

### 14. Waveforms transfer characteristics



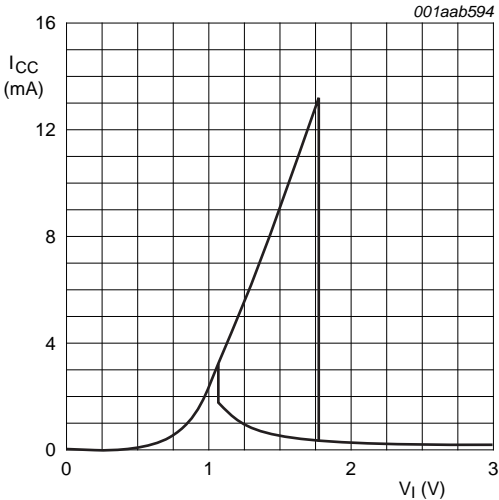


Fig 18. Typical 74LVC1G58 transfer characteristics;  $V_{CC} = 3.0$  V

15. Package outline

Plastic surface-mounted package; 6 leads

SOT363

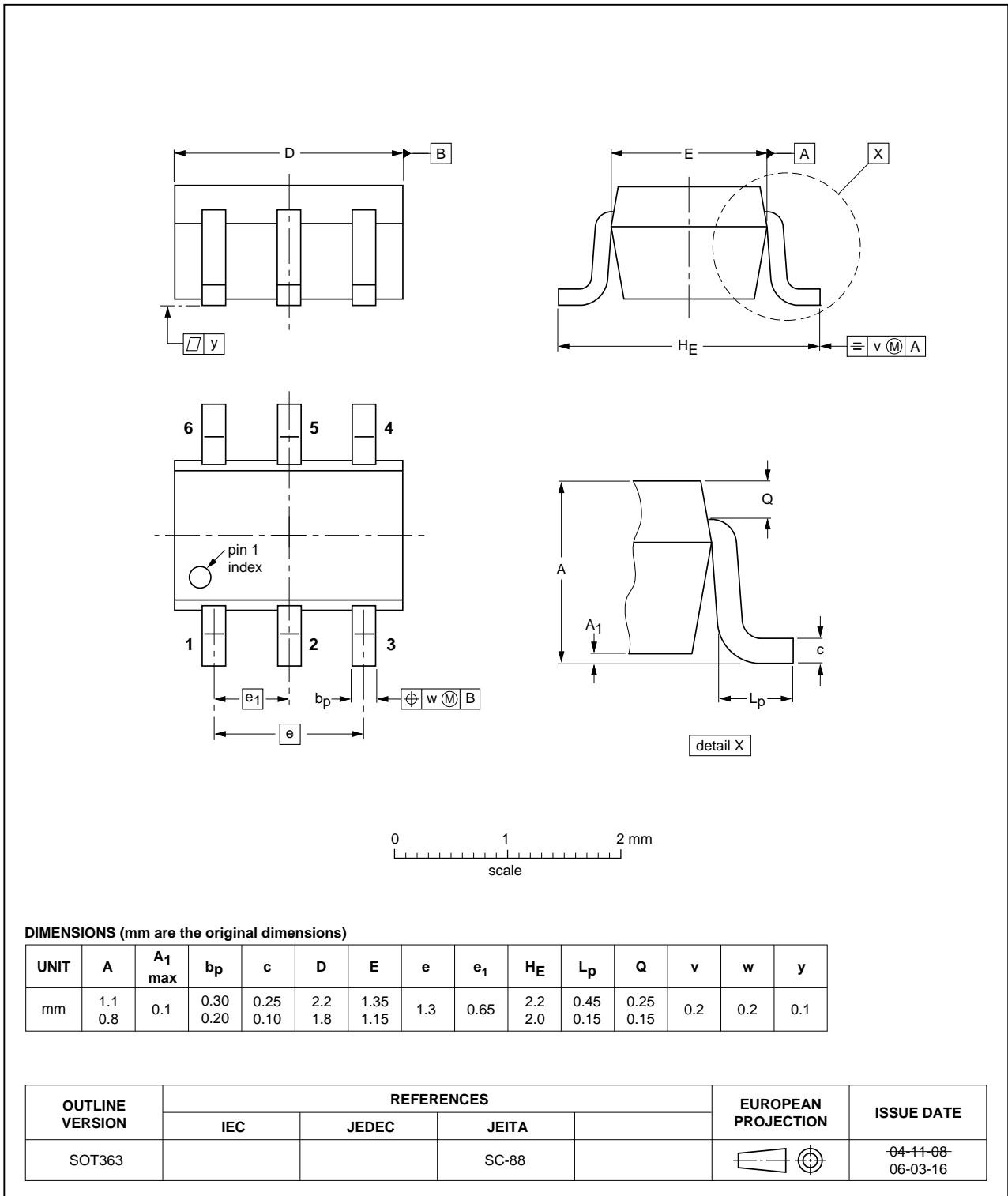


Fig 19. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

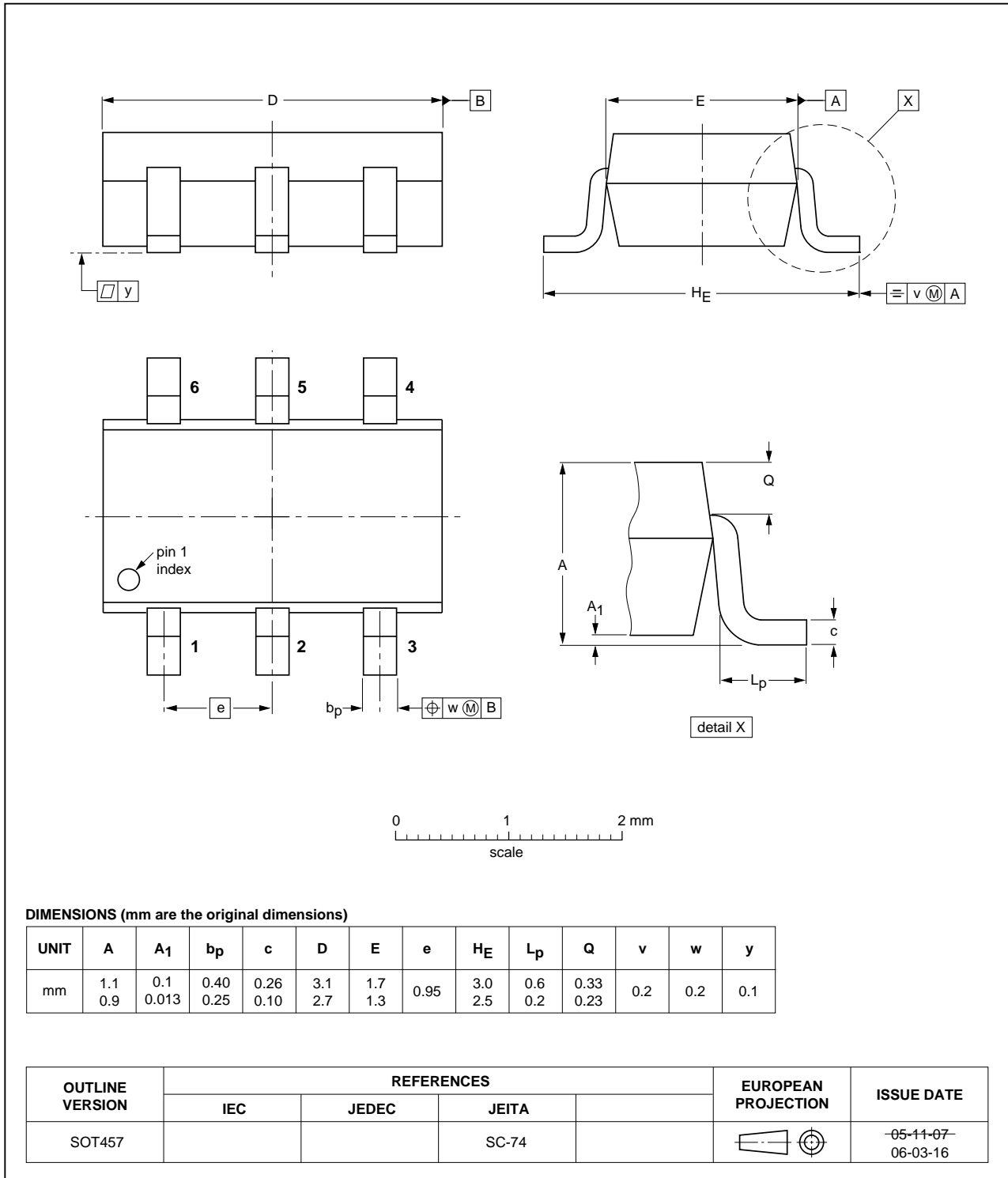


Fig 20. Package outline SOT457 (TSOP6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

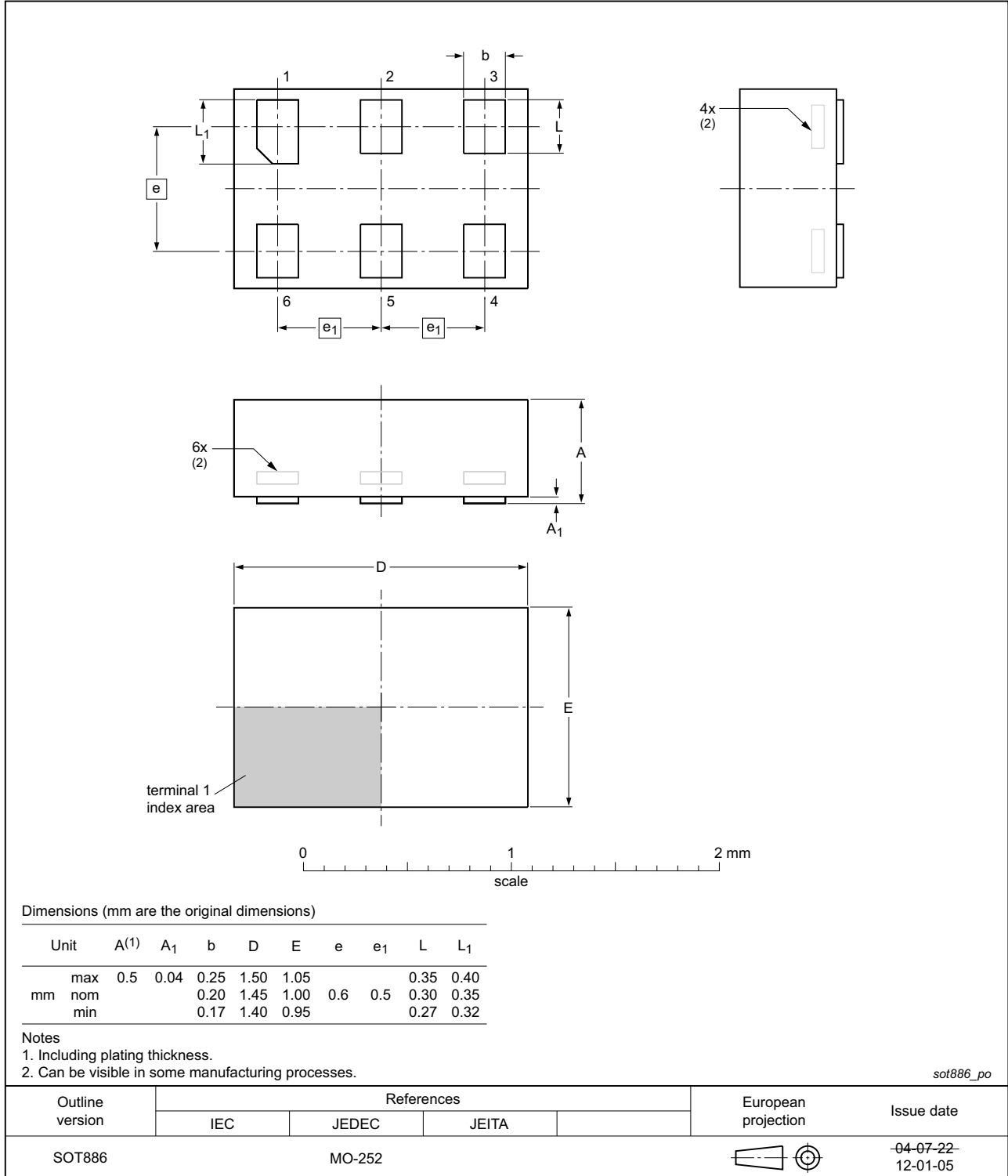


Fig 21. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

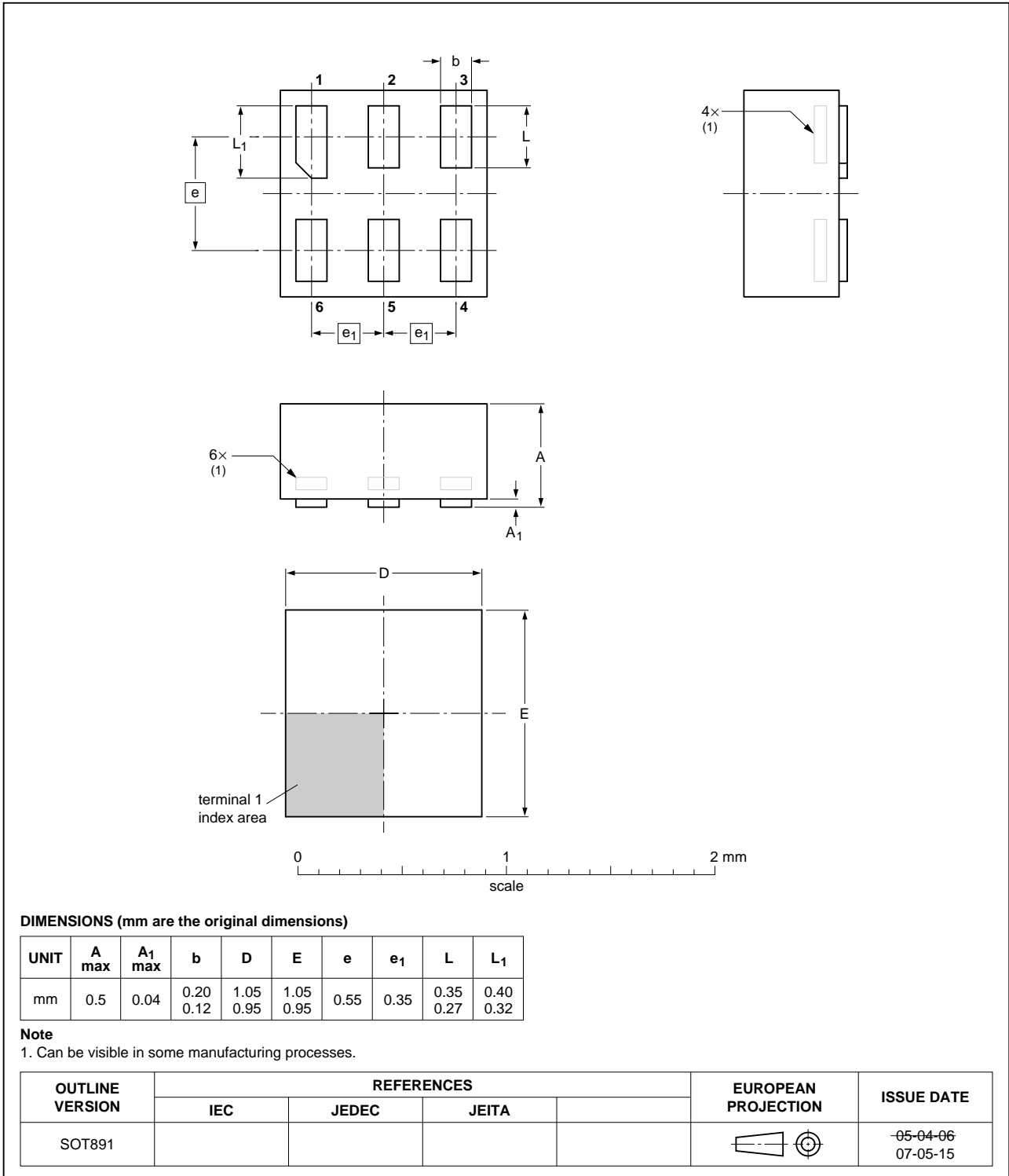


Fig 22. Package outline SOT891 (XSON6)

**XSON6: extremely thin small outline package; no leads;  
6 terminals; body 0.9 x 1.0 x 0.35 mm**

SOT1115

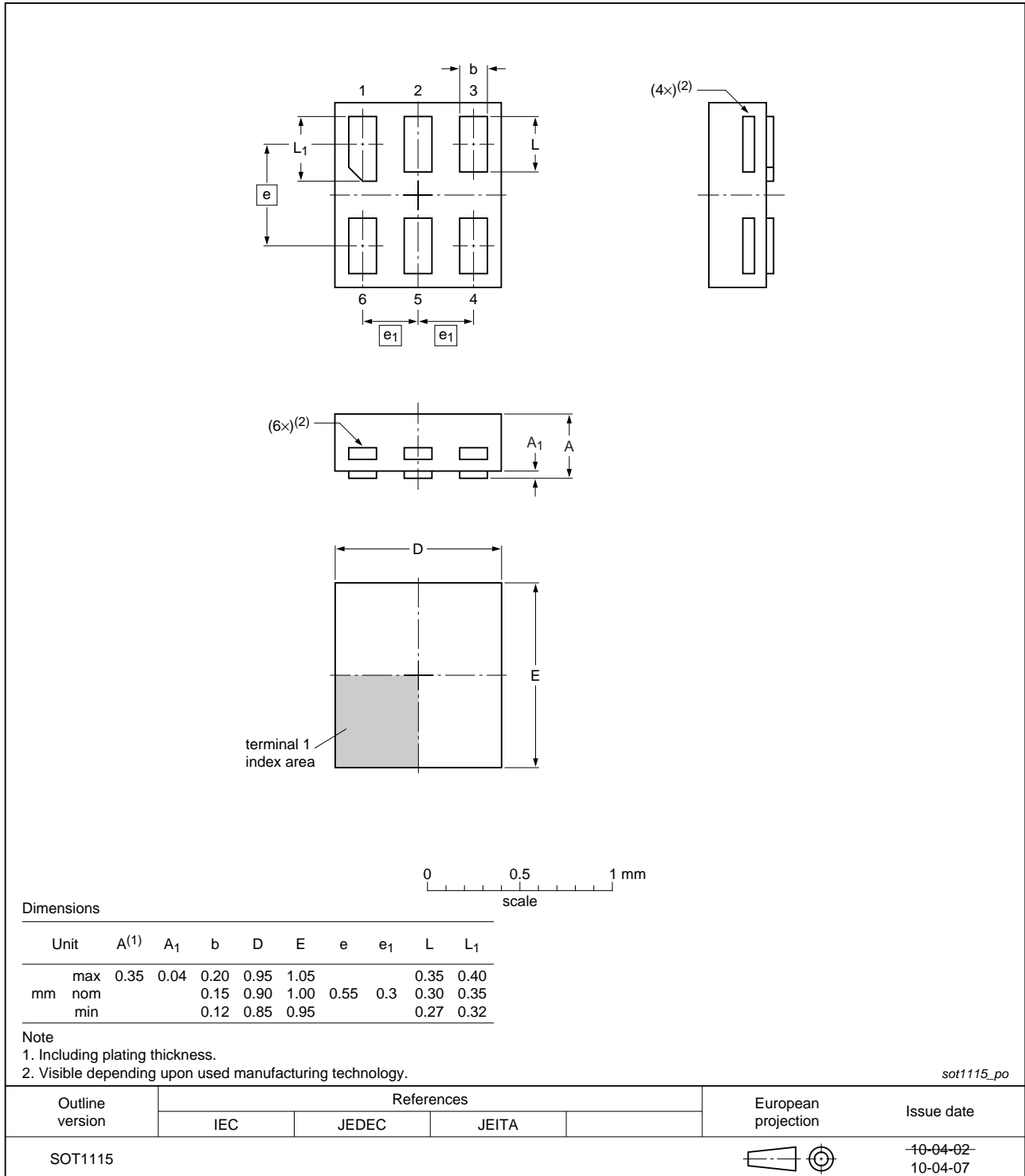


Fig 23. Package outline SOT1115 (XSON6)



**XSON6: extremely thin small outline package; no leads;  
6 terminals; body 1.0 x 1.0 x 0.35 mm**

SOT1202



Fig 24. Package outline SOT1202 (XSON6)

## 16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G58 v.8	20140422	Product data sheet	-	74LVC1G58 v.7
Modifications:	<ul style="list-style-type: none"> <li>Package outline drawing of SOT886 (<a href="#">Figure 21</a>) modified.</li> </ul>			
74LVC1G58 v.7	20111206	Product data sheet	-	74LVC1G58 v.6
Modifications:	<ul style="list-style-type: none"> <li>Legal pages updated.</li> </ul>			
74LVC1G58 v.6	20110923	Product data sheet	-	74LVC1G58 v.5
74LVC1G58 v.5	20101015	Product data sheet	-	74LVC1G58 v.4
74LVC1G58 v.4	20090427	Product data sheet	-	74LVC1G58 v.3
74LVC1G58 v.3	20070827	Product data sheet	-	74LVC1G58 v.2
74LVC1G58 v.2	20070222	Product data sheet	-	74LVC1G58 v.1
74LVC1G58 v.1	20040915	Product data sheet	-	-

## 18. Legal information

### 18.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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